

Inchange Semiconductor

Product Specification

Silicon PNP Power Transistors

2SA886

DESCRIPTION

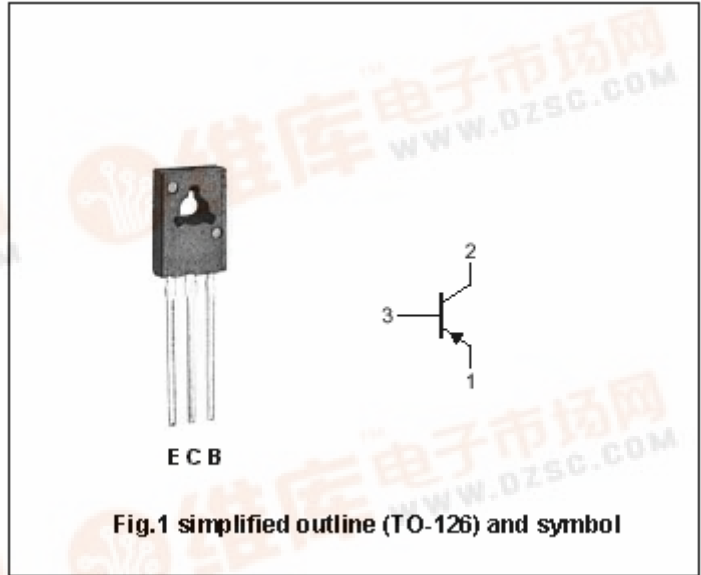
- With TO-126 package
- Complement to type 2SC1847
- Low collector-emitter saturation voltage

APPLICATIONS

- For low-frequency power amplification

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base



Absolute Maximum Ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-50	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-40	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-1.5	A
I <sub>CM</sub>	Collector current-peak		-3.0	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	1.2* <sup>1</sup>	W
			5* <sup>2</sup>	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

Note) \*1: Without heat sink

\*2: With a 100 × 100 × 2 mm A1 heat sink

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-2mA; I <sub>B</sub> =0	-40			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA; I <sub>E</sub> =0	-50			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-1.5A; I <sub>B</sub> =-0.15A			-1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-2A; I <sub>B</sub> =-0.2A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-20V; I <sub>E</sub> =0			-1	μ A
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =-10V; I <sub>B</sub> =0			-100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-10	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V	80		220	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-20V; f=1MHz		45		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A; V <sub>CB</sub> =-5V; f=200MHz		150		MHz

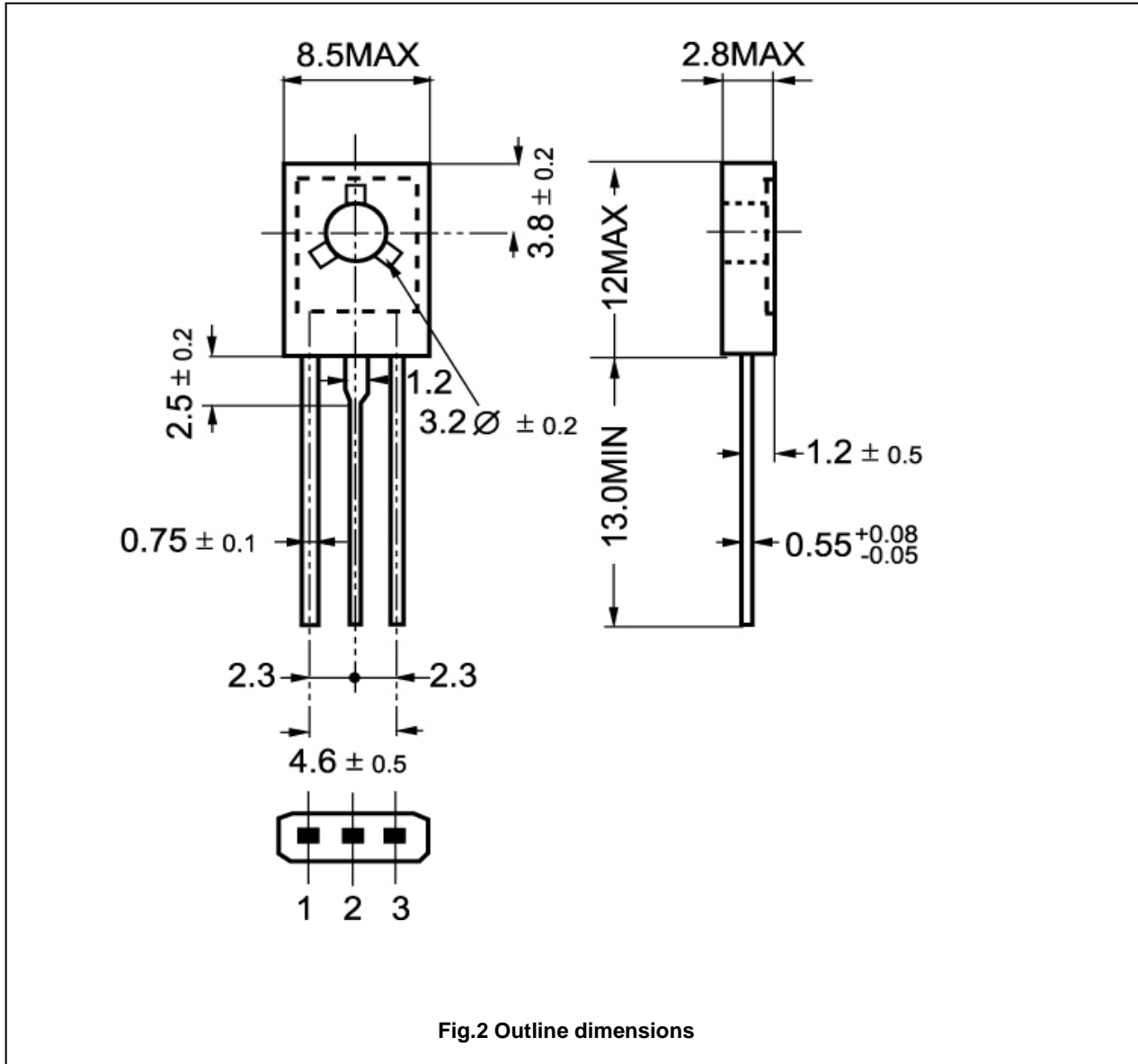
◆ h<sub>FE</sub> Classifications

Q	R
80-160	120-220

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PACKAGE OUTLINE



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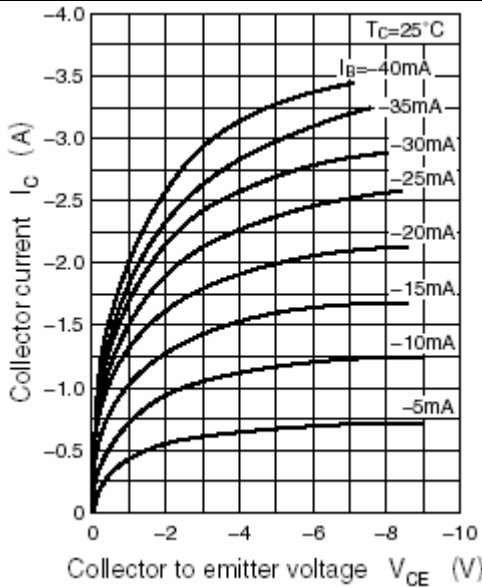


Fig.3 Static Characteristic

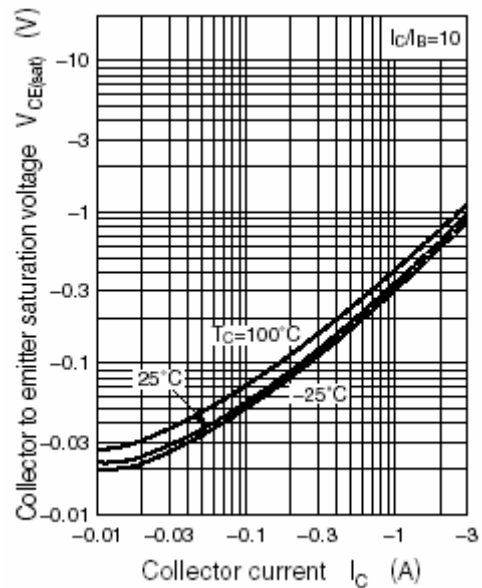


Fig.4 Collector-Emitter Saturation Voltage

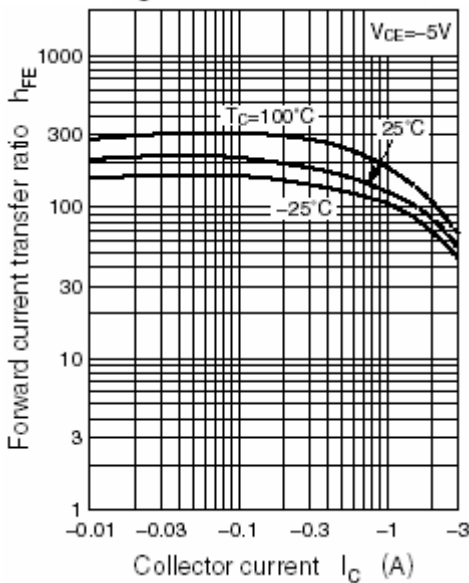


Fig.5 DC current Gain

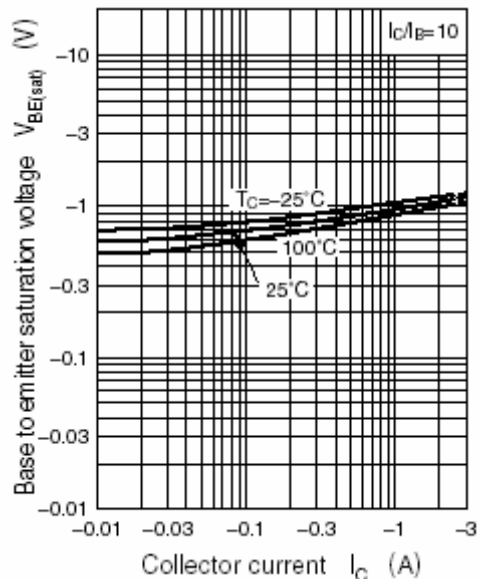


Fig.6 Base-Emitter Saturation Voltage

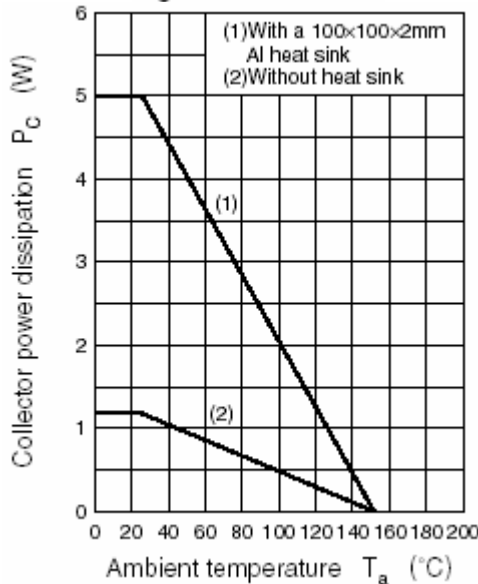


Fig.7 Power Derating

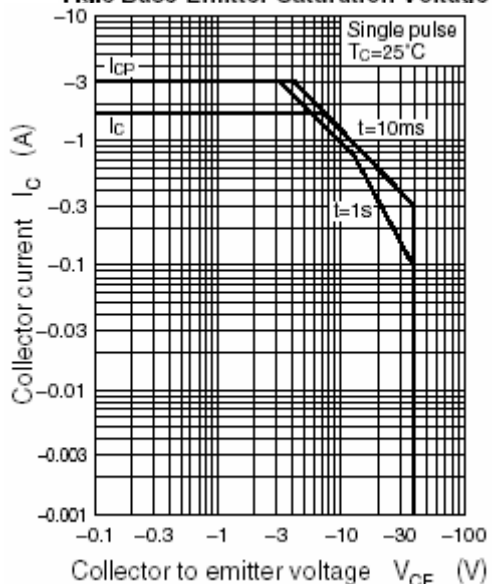


Fig.8 Safe Operating Area